

WHAT IS CLAIMED IS:

1. A semiconductor integrated circuit device including

5 a plurality of internal circuits for processing signals individually; and

a plurality of signal lines connected individually with said internal circuits, a first voltage line for feeding a first voltage to said
10 internal circuits, and a second voltage line for feeding a second voltage to said internal circuits, comprising:

a first protective circuit connected between the signal lines and said first voltage line of each of
15 said internal circuits for allowing an electric current to flow from said first voltage line to said signal lines at a protection time against an electrostatic breakdown;

a second protective circuit connected between
20 the signal lines and said second voltage line of each of said internal circuits for allowing an electric current to flow from said signal lines to said second voltage line at a protection time against an electrostatic breakdown;

25 a third protective circuit connected between the

signal lines and said first voltage line of each of
said internal circuits for allowing an electric
current to flow from said signal lines to said first
voltage line at a protection time against an
5 electrostatic breakdown; and

a fourth protective circuit connected between
the signal lines and said second voltage line of each
of said internal circuits for allowing an electric
current to flow from said second voltage line to said
10 signal lines at a protection time against an
electrostatic breakdown.

2. A semiconductor integrated circuit device
according to Claim 1,

15 wherein said first protective circuit, said
second protective circuit, said third protective
circuit and said fourth protective circuit
individually allow no electric current to flow when
said internal circuits are active.

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3. A semiconductor integrated circuit device
according to Claim 2,

wherein one of said first protective circuit,
said second protective circuit, said third protective
25 circuit and said fourth protective circuit includes a

plurality of diodes connected in series with one another.

4. A semiconductor integrated circuit device
5 according to Claim 3,

wherein each of said third protective circuit and said fourth protective circuit includes a plurality of diodes connected in series with one another.

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5. A semiconductor integrated circuit device
according to Claim 3,

15 wherein said first protective circuit and said second protective circuit include a breakdown protective circuit by a surface breakdown and a breakdown protective circuit by a source-follower transistor.

6. A semiconductor integrated circuit device
20 according to Claim 5,

wherein said first protective circuit and said second protective circuit include a protective circuit having the breakdown protective circuit and a diode connected in series.

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7. A semiconductor integrated circuit device according to Claim 1,

wherein the first one of said internal circuits is a high-frequency circuit, and

5 wherein the second one of said internal circuits is a low-frequency circuit.

8. A semiconductor integrated circuit device according to Claim 7,

10 wherein said third protective circuit and said fourth protective circuit, as connected with the signal lines of said high-frequency circuit, include a circuit having a plurality of diodes connected in series, and

15 wherein said third protective circuit and said fourth protective circuit, as connected with the signal lines of said low-frequency circuit, include one diode.

20 9. A semiconductor integrated circuit device according to Claim 3,

wherein said diodes are formed of diode-connected transistors.

25 10. A semiconductor integrated circuit device

according to Claim 9,

wherein said diode-connected transistors are electrically isolated from one another by a barrier of an insulator.

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11. A semiconductor integrated circuit device according to Claim 1,

wherein said semiconductor integrated circuit device is one for a wireless communication system.

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